



**SDI FINAL EVALUATION FORM 1.1**

**PART 1:**

Journal Name:	<a href="#">Physical Science International Journal</a>
Manuscript Number:	2015_PSIJ_17567
Title of the Manuscript:	Modeling and Simulation of High Blocking Voltage in 4H Silicon Carbide Bipolar Junction Transistors
Type of Article	

**PART 2:**

FINAL EVALUATOR'S comments on revised paper (if any)	Authors' response to final evaluator's comments
The authors improved well the manuscript. This version could be published.	

**Reviewer Details:**

Name:	Anonymous
Department, University & Country	Mohamed Premier University, Morocco